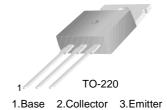


## TIP145T/146T/147T

## Monolithic Construction With Built In Base-Emitter Shunt Resistors

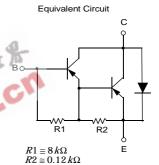
- High DC Current Gain :  $h_{FE} = 1000@V_{CE} = -4V$ ,  $I_{C} = -5A$  (Min.)
- Industrial Use
- Complement to TIP140T/141T/142T



# **PNP Epitaxial Silicon Darlington Transistor**

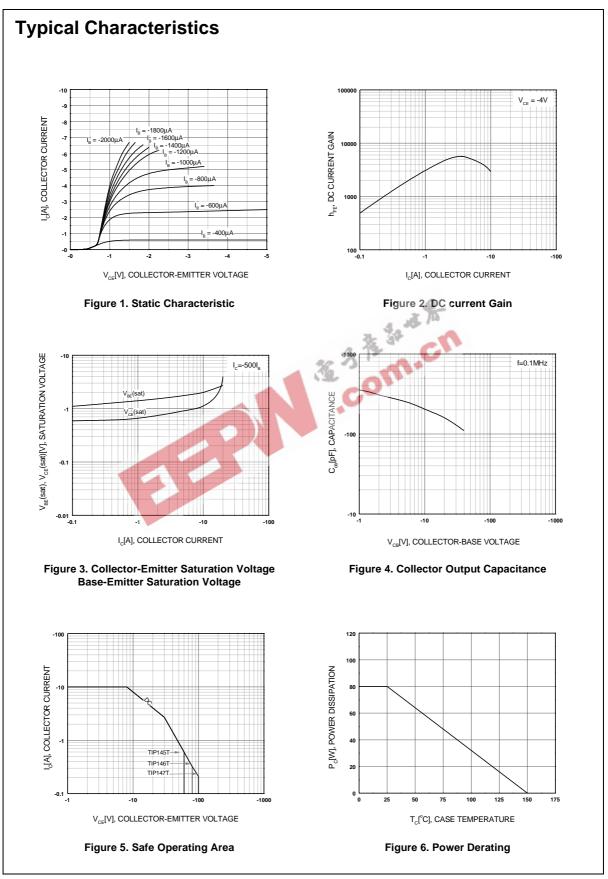
## Absolute Maximum Ratings T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage : TIP145T	- 60	V
	: TIP146T	- 80	V
	: TIP147T	- 100	V
	Collector-Emitter Voltage : TIP145T	- 60	V
$V_{CEO}$	: TIP146T	- 80	V
	: TIP147T	- 100	V
V <sub>EBO</sub>	Emitter-Base Voltage	- 5	V
I <sub>C</sub>	Collector Current (DC)	- 10	A
I <sub>CP</sub>	Collector Current (Pulse)	- 15	Α
I <sub>B</sub>	Base Current (DC)	- 0.5	Α
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> =25°C)	80	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	- 65 ~ 150	°C



# Electrical Characteristics $T_C=25$ °C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
V <sub>CEO</sub> (sus)	Collector-Emitter Sustaining Voltage : TIP145T : TIP146T : TIP147T	I <sub>C</sub> = - 30mA, I <sub>B</sub> = 0	- 60 - 80 - 100			V V V
I <sub>CEO</sub>	Collector Cut-off Current : TIP145T : TIP146T : TIP147T	$V_{CE} = -30V, I_{B} = 0$ $V_{CE} = -40V, I_{B} = 0$ $V_{CE} = -50V, I_{B} = 0$			- 2 - 2 - 2	mA mA mA
I <sub>CBO</sub>	Collector Cut-off Current : TIP145T : TIP146T : TIP147T	$V_{CB} = -60V, I_{E} = 0$ $V_{CB} = -80V, I_{E} = 0$ $V_{CB} = -100V, I_{E} = 0$			- 1 - 1 - 1	mA mA mA
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{BE} = -5V, I_{C} = 0$			- 2	mA
h <sub>FE</sub>	DC Current Gain	V <sub>CE</sub> = - 4V, I <sub>C</sub> = - 5A V <sub>CE</sub> = - 4V, I <sub>C</sub> = - 10A	1000 500			
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	$I_C = -5A$ , $I_B = -10mA$ $I_C = -10A$ , $I_B = -40mA$			- 2 - 3	V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	I <sub>C</sub> = - 10A, I <sub>B</sub> = - 40mA			- 3.5	V
V <sub>BE</sub> (on)	Base-Emitter On Voltage	V <sub>CE</sub> = - 4V, I <sub>C</sub> = - 10A			- 3	V
t <sub>D</sub>	Delay Time	$V_{CC} = -30V, I_{C} = -5A$		0.15		μs
t <sub>R</sub>	Rise Time	$I_{B1} = -20 \text{mA}, I_{B2} = 20 \text{mA}$		0.55		μs
t <sub>STG</sub>	Storage Time	$R_L = 6\Omega$		2.5		μs
t <sub>F</sub>	Fall Time			2.5		μs



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# **Package Dimensions** TO-220 4.50 ±0.20 9.90 ±0.20 (8.70) $1.30 \pm 0.10$ $2.80 \pm 0.10$ (1.70) 1.30 +0.10 -0.05 $\emptyset 3.60 \pm 0.10$ 15.30 ±0.20 18.95MAX. (3.70) 9.20 ±0.20 (1.46) 13.08 ±0.20 10.08 ±0.30 0.80 ±0.10 0.50 +0.10 -0.05 2.40 ±0.20 2.54TYP 2.54TYP [2.54 ±0.20] [2.54 ±0.20] 10.00 ±0.20 Dimensions in Millimeters

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CoolFET™	FASTr™	MicroFET™	PowerTrench <sup>®</sup>	SuperSOT™-6
CROSSVOLT™	FRFET™	MicroPak™	QFET™	SuperSOT™-8
DOME™	GlobalOptoisolator™	MICROWIRE™	QS™	SyncFET™
EcoSPARK™	GTO™	MSX™	QT Optoelectronics™	TinyLogic™
E2CMOSTM	HiSeC™	MSXPro™	Quiet Series™	TruTranslation™
EnSigna™	$I^2C^{TM}$	$OCX^{TM}$	RapidConfigure™	UHC™
Across the board.	. Around the world.™	OCXPro™	RapidConnect™	UltraFET <sup>®</sup>
The Power Franchise™		OPTOLOGIC <sup>®</sup>	SILENT SWITCHER®	$VCX^{TM}$
Programmable Active Droop™		OPTOPLANAR™	SMART START™	

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